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HSML, P.C.

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S/N 10/757,864

PATENTIN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	KITAOKA, et al.	Examiner:	M. Song
Serial No.:	10/757,864	Group Art Unit:	1722
Filed:	January 15, 2004	Docket No.:	10873.1391US01
Title:	METHOD OF MANUFACTURING GROUP III NITRIDE SUBSTRATE AND SEMICONDUCTOR DEVICE		

CERTIFICATE UNDER 37 CFR 1.6(d):

I hereby certify that this paper is being transmitted by facsimile to the U.S. Patent and Trademark Office on January 23, 2007.

By: Peggy J. Karkhove  
Name: Peggy J. Karkhove

COMMUNICATION REGARDING FORM 1449

Mail Stop ISSUE FEE  
Commissioner for Patents  
P. O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir or Madam:

Pertaining to the above-referenced patent application, Applicants respectfully assert that on November 27, 2006 an Information Disclosure Statement was electronically filed with the United States Patent and Trademark Office. However, the Form 1449 has not been returned to the undersigned as being considered by the Examiner. Pursuant to the provisions of M.P.E.P. 609, it is requested that the attached Form 1449, marked as being considered and initialed by the Examiner, be returned to the undersigned with an official communication.

Respectfully submitted,

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Dated: January 23, 2007

By: Douglas P. Mueller  
Reg. No. 30,300

DPM/pjk

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## INFORMATION DISCLOSURE STATEMENT

IN AN APPLICATION

(Use several sheets if necessary)

Docket Number:

10873.1391US01

Application Number:

10/757,864

Applicant: KITAOKA et al.

Filing Date: January 15, 2004

Group Art Unit: 1722

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	5,868,837	February, 1999	DiSalvo et al.			
	6,121,121	September, 2000	Koide			
	6,270,569	August, 2001	Shibata, et al.			
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	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
	11-145516	May, 1999	Japan				
	2000-357663	December, 2000	Japan			Abstract	
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## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	Kawamura et al., "Growth of a Large GaN single Crystal Using the Liquid Phase Epitaxy (LPE) Technique" Japanese Journal of Applied Physics Vol. 42 (2003) pp. L4-L6
	M. Morishita, et al. "The growth mechanism of GaN singles crystals in Na flux system", Journal of the Japanese association for crystal growth, Vol. 30, No. 3 (2003), 801aA7
	M. Morishita, et al., "Growth of transparent GaN single crystals using LPE technique in Na flux system", The Japan Society of Applied Physics and Related Societies, Extended Abstracts (The 51st Spring Meeting, 2004), 29 p-YK-6

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EXAMINER

DATE CONSIDERED

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.

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